COMPLIANT

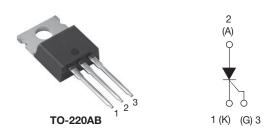
HALOGEN

**FREE** 



### Vishay Semiconductors

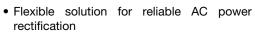
# **High Voltage, Phase Control Thyristor, 12 A**

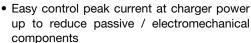


PRIMARY CHARACTERISTICS							
I <sub>T(AV)</sub> 8 A							
V <sub>DRM</sub> /V <sub>RRM</sub>	800 V						
V <sub>TM</sub>	1.2 V						
I <sub>GT</sub>	15 mA						
TJ	-40 to +125 °C						
Package TO-220AB							
Circuit configuration	Single SCR						

#### **FEATURES**

- AEC-Q101 qualified
- Meets JESD 201 class 1A whisker test





• Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

### **APPLICATIONS**

- On-board and off-board EV / HEV battery chargers
- Renewable energy inverters

#### **DESCRIPTION**

The VS-12TTS08HM3 high voltage series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications.

OUTPUT CURRENT IN TYPICAL APPLICATIONS								
APPLICATIONS SINGLE-PHASE BRIDGE THREE-PHASE BRIDGE UNITS								
Capacitive input filter T <sub>A</sub> = 55 °C, T <sub>J</sub> = 125 °C, common heatsink of 1 °C/W	13.5	17	А					

MAJOR RATINGS AND CHARACTERISTICS								
PARAMETER	TEST CONDITIONS	VALUES	UNITS					
I <sub>T(AV)</sub>	Sinusoidal waveform	8	Δ.					
I <sub>T(RMS)</sub>		12.5	A					
$V_{RRM}/V_{DRM}$		800	V					
I <sub>TSM</sub>		110	А					
V <sub>T</sub>	8 A, T <sub>J</sub> = 25 °C	1.2	V					
dV/dt		150	V/µs					
dl/dt		100	A/µs					
T <sub>J</sub>	Range	-40 to +125	°C					

VOLTAGE RATINGS									
PART NUMBER	V <sub>RRM</sub> , MAXIMUM PEAK REVERSE VOLTAGE V	V <sub>DRM</sub> , MAXIMUM PEAK DIRECT VOLTAGE V	I <sub>RRM</sub> / I <sub>DRM</sub> AT 125 °C mA						
VS-12TTS08HM3	800	800	5.0						



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ABSOLUTE MAXIMUM RATINGS								
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS				
Maximum average on-state current	I <sub>T(AV)</sub>	T = 100 °C 190° conduction half sine ways	8					
Maximum RMS on-state current	I <sub>T(RMS)</sub>	T <sub>C</sub> = 108 °C, 180° conduction, half sine wave	12.5	Α				
Maximum peak one-cycle	1	10 ms sine pulse, rated V <sub>RRM</sub> applied, T <sub>J</sub> = 125 °C	95	A				
non-repetitive surge current	I <sub>TSM</sub>	10 ms sine pulse, no voltage reapplied, T <sub>J</sub> = 125 °C	110					
Maximum I <sup>2</sup> t for fusing	l <sup>2</sup> t	10 ms sine pulse, rated $V_{RRM}$ applied, $T_J$ = 125 °C	45	A <sup>2</sup> s				
Maximum i-t for fusing	I-t	10 ms sine pulse, no voltage reapplied, T <sub>J</sub> = 125 °C	64					
Maximum I <sup>2</sup> √t for fusing	I <sup>2</sup> √t	$t = 0.1$ ms to 10 ms, no voltage reapplied, $T_J = 125$ °C	640	A²√s				
Maximum on-state voltage drop	$V_{TM}$	8 A, T <sub>J</sub> = 25 °C	1.2	V				
On-state slope resistance	r <sub>t</sub>	T <sub>.1</sub> = 125 °C	16.2	mΩ				
Threshold voltage	V <sub>T(TO)</sub>	1J = 123 0	0.87	V				
Maximum reverse and direct leakage current	1/1	$T_J = 25  ^{\circ}\text{C}$	0.05					
Maximum reverse and direct leakage current	I <sub>RM</sub> /I <sub>DM</sub>	$V_R = \text{rated } V_{RRM} / V_{DRM}$	5.0					
Typical holding current	I <sub>H</sub>	Anode supply = 6 V, resistive load, initial $I_T$ = 1 A, $T_J$ = 25 °C	30	mA				
Typical latching current	ΙL	Anode supply = 6 V, resistive load, T <sub>J</sub> = 25 °C	50					
Maximum rate of rise of off-state voltage	dV/dt	$T_J = T_J \text{ max., linear to } 80 \text{ %, } V_{DRM} = R_g - k = \text{open}$	150	V/µs				
Maximum rate of rise of turned-on current	dl/dt		100	A/µs				

TRIGGERING							
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Maximum peak gate power	P <sub>GM</sub>		8.0	W			
Maximum average gate power	P <sub>G(AV)</sub>		2.0	VV			
Maximum peak positive gate current	+I <sub>GM</sub>		1.5	Α			
Maximum peak negative gate voltage	-V <sub>GM</sub>		10	V			
		Anode supply = 6 V, resistive load, T <sub>J</sub> = - 65 °C	20	mA			
Maximum required DC gate current to trigger	$I_{GT}$	Anode supply = 6 V, resistive load, T <sub>J</sub> = 25 °C	15				
		Anode supply = 6 V, resistive load, T <sub>J</sub> = 125 °C	10				
		Anode supply = 6 V, resistive load, T <sub>J</sub> = -65 °C	1.2				
Maximum required DC gate voltage to trigger	$V_{GT}$	Anode supply = 6 V, resistive load, T <sub>J</sub> = 25 °C		V			
		Anode supply = 6 V, resistive load, T <sub>J</sub> = 125 °C	0.7	V			
Maximum DC gate voltage not to trigger	$V_{GD}$	T = 105 °C V = reted value	0.2				
Maximum DC gate current not to trigger	I <sub>GD</sub>	T <sub>J</sub> = 125 °C, V <sub>DRM</sub> = rated value	0.1	mA			

SWITCHING							
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Typical turn-on time	t <sub>gt</sub>	T <sub>J</sub> = 25 °C	0.8				
Typical reverse recovery time	t <sub>rr</sub>	T <sub>.I</sub> = 125 °C	3	μs			
Typical turn-off time	t <sub>q</sub>	1J = 125 O	100				



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THERMAL AND MECHANICAL SPECIFICATIONS							
PARAMETER	ARAMETER SYMBOL TEST CONDITIONS			UNITS			
Maximum junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-40 to +125	°C			
Maximum thermal resistance, junction to case	R <sub>thJC</sub>	DC operation	1.5				
Maximum thermal resistance, junction to ambient	R <sub>thJA</sub>		62	°C/W			
Typical thermal resistance, case to heatsink R <sub>thC</sub>		Mounting surface, smooth, and greased	0.5				
Approximate weight			2	g			
Approximate weight			0.07	oz.			
Mounting torque	minimum		6 (5)	kgf · cm			
iviounting torque	maximum		12 (10)	(lbf ⋅ in)			
Marking device Case style To		Case style TO-220AB	12TT:	S08H			

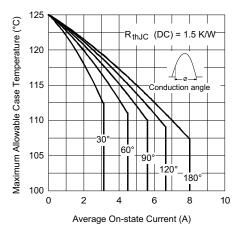


Fig. 1 - Current Rating Characteristics

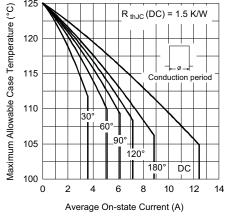


Fig. 2 - Current Rating Characteristics

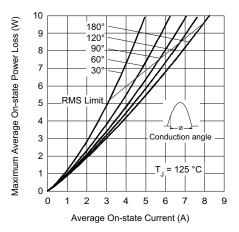


Fig. 3 - On-State Power Loss Characteristics

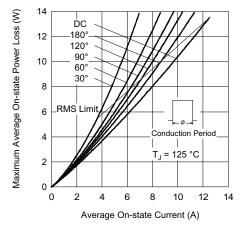


Fig. 4 - On-State Power Loss Characteristics

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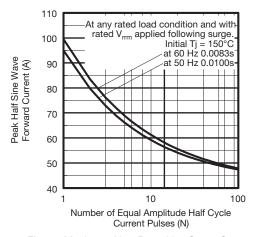


Fig. 5 - Maximum Non-Repetitive Surge Current

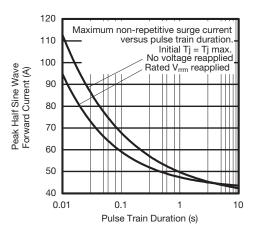


Fig. 6 - Maximum Non-Repetitive Surge Current

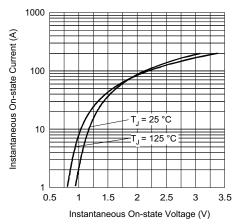


Fig. 7 - On-State Voltage Drop Characteristics

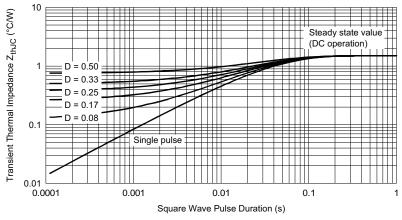


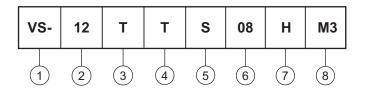
Fig. 8 - Thermal Impedance  $Z_{\text{thJC}}$  Characteristics



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### **ORDERING INFORMATION TABLE**

**Device code** 



1 - Vishay Semiconductors product

Current rating (12.5 A)

3 - Circuit configuration:

T = single thyristor

4 - Package:

T = TO-220

5 - Type of silicon:

S = standard recovery rectifier

6 - Voltage rating (08 = 800 V)

7 - H = AEC-Q101 qualified

8 - Environmental digit:

M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

ORDERING INFORMATION (Example)								
PREFERRED P/N QUANTITY PER T/R MINIMUM ORDER QUANTITY PACKAGING DESCRIPTION								
VS-12TTS08HM3	50	1000	Antistatic plastic tube					

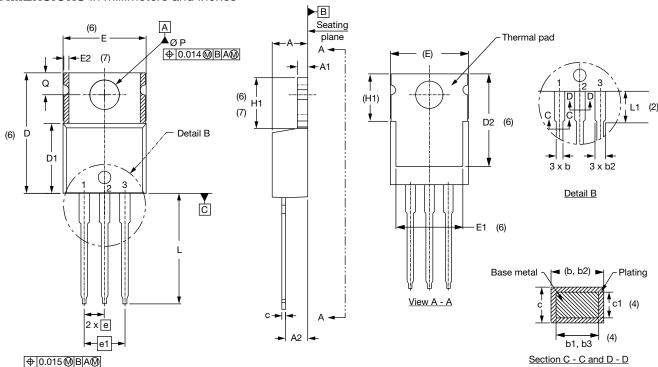
LINKS TO RELATED DOCUMENTS					
Dimensions <u>www.vishay.com/doc?95222</u>					
Part marking information	www.vishay.com/doc?95028				

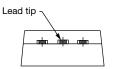


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### **TO-220AB**

### **DIMENSIONS** in millimeters and inches





### Conforms to JEDEC® outline TO-220AB

SYMBOL	MILLIM	IETERS	INC	HES	NOTES	NOTES	SYMBOL	MILLIM	IETERS	INC	HES	NOTES
STIVIDOL	MIN.	MAX.	MIN.	MAX.	NOTES		STINIBUL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.25	4.65	0.167	0.183			D2	11.68	12.88	0.460	0.507	6
A1	1.14	1.40	0.045	0.055			E	10.11	10.51	0.398	0.414	3, 6
A2	2.56	2.92	0.101	0.115			E1	6.86	8.89	0.270	0.350	6
b	0.69	1.01	0.027	0.040			E2	-	0.76	-	0.030	7
b1	0.38	0.97	0.015	0.038	4		е	2.41	2.67	0.095	0.105	
b2	1.20	1.73	0.047	0.068			e1	4.88	5.28	0.192	0.208	
b3	1.14	1.73	0.045	0.068	4		H1	5.84	6.86	0.230	0.270	6, 7
С	0.36	0.61	0.014	0.024			L	13.52	14.02	0.532	0.552	
c1	0.36	0.56	0.014	0.022	4		L1	3.32	3.82	0.131	0.150	2
D	14.85	15.25	0.585	0.600	3		ØΡ	3.54	3.73	0.139	0.147	
D1	8.38	9.02	0.330	0.355			Q	2.60	3.00	0.102	0.118	

#### Notes

- (1) Dimensioning and tolerancing as per ASME Y14.5M-1994
- (2) Lead dimension and finish uncontrolled in L1
- (3) Dimension D, D1 and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Dimension b1, b3 and c1 apply to base metal only
- (5) Controlling dimensions: inches
- (6) Thermal pad contour optional within dimensions E, H1, D2 and E1
- (7) Dimensions E2 x H1 define a zone where stamping and singulation irregularities are allowed
- (8) Outline conforms to JEDEC® TO-220, except A2 (maximum) and D2 (minimum) where dimensions are derived from the actual package outline



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